

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A ferroelectric film that is described by a general formula $AB_{1-x}Nb_xO_3(Pb,A)(B_{1-x}Nb_x)O_3$,

wherein an A element ~~includes~~ comprises at least ~~Pb~~ one of La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu,

wherein a B element ~~includes~~ comprises at least one of Zr, Ti, V, W, Hf and Ta, and

wherein ~~Nb_x~~ is ~~included~~ within the range of: $0.05 \leq x \leq 0.4$.

2. (Currently Amended) ~~The A ferroelectric film as defined by claim 1 that is described by~~ $(Pb_{1-y}A_y)(B_{1-x}Nb_x)O_3$,

wherein ~~the an~~ A element includes ~~Pb_{1-y}Ln_y~~ comprises at least one of La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu, and

wherein ~~Ln includes at least one of La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu,~~ and y is within the range of: $0 < y \leq 0.2$,

wherein a B element comprises at least one of Zr, Ti, V, W, Hf and Ta, and

wherein x is within the range of: $0.05 \leq x \leq 0.4$.

3-7. (Canceled)

8. (Currently Amended) ~~The PZT family ferroelectric film as defined by claim 51,~~ comprising:

~~Si, Ge or Si and Ge of at least 0.5 mol%.~~

9. (Currently Amended) ~~The PZT family ferroelectric film as defined by claim 51,~~ comprising:

Si, Ge or Si and Ge of at least from about 0.5 mol% and less than to about 5
mol%.

10-23. (Canceled)

24. (Currently Amended) A ferroelectric memory ~~manufactured by using the~~
~~manufacture method as defined by any one of claims 1 to 13~~ device comprising:

a substrate;

a transistor formed on the substrate; and

a ferroelectric capacitor formed above the substrate,

wherein the ferroelectric capacitor comprises a ferroelectric film as defined by
claim 1.

25. (Currently Amended) A piezoelectric ~~element~~ actuator comprising the
~~ferroelectric film as defined by any one of claims 1 to 13 or the ferroelectric capacitor as~~
~~defined by claim 23:~~

a substrate; and

a piezoelectric element formed above the substrate,

wherein the piezoelectric element comprises a ferroelectric film as defined by
claim 1.

26. (Canceled)

27. (New) The ferroelectric film as defined by claim 2, comprising:

Si, Ge or Si and Ge.

28. (New) The ferroelectric film as defined by claim 2, comprising:

Si, Ge or Si and Ge of from about 0.5 mol% to about 5 mol%.

29. (New) A ferroelectric memory device comprising:

a substrate;

a transistor formed on the substrate; and

a ferroelectric capacitor formed above the substrate,
wherein the ferroelectric capacitor comprises a ferroelectric film as defined by
claim 2.

30. (New) A piezoelectric actuator comprising:
a substrate; and
a piezoelectric element formed above the substrate,
wherein the piezoelectric element comprises a ferroelectric film as defined by
claim 2.